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ADD-A-PAK Gen 7 Power Modules Standard Diodes, 60 A



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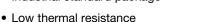
PRODUCT SUMMARY					
I _{F(AV)}	60 A				
Туре	Modules - Diode, High Voltage				
Package	ADD-A-PAK Gen 7				
Circuit	Two diodes doubler circuit, two diodes common cathode, two diodes common anode, single diode				

MECHANICAL DESCRIPTION

The ADD-A-PAK Gen 7, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- · High voltage
- Industrial standard package



- UL approved file E78996
 Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- · Easy mounting on heat sink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	VALUES	UNITS				
I _{F(AV)}	114 °C	60					
I _{F(RMS)}		94	1				
1	50 Hz	1300	Α				
I _{FSM}	60 Hz	1360	7				
l ² t	50 Hz	8.44	1.42-				
1-1	60 Hz	7.68	kA ² s				
I ² √t		84.5	kA²√s				
V _{RRM}	Range	400 to 1600	V				
T _J		-40 to +150	°C				
T _{Stg}		-40 to +150	°C				



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J = 150 °C mA				
	04	400	500					
	06	600	700					
	08	800	900					
VS-VSK.56	10	1000	1100	10				
	12	1200	1300					
	14	1400	1500					
	16	1600	1700					

FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average forward current	I _{F(AV)}	180° condu	ction, half sine	wave	60	А
at case temperature	'F(AV)	100 001100	otion, nan sine	wavo	114	°C
Maximum RMS forward current	I _{F(RMS)}	DC at 90 °C	case temperat	ure	94	
		t = 10 ms	No voltage		1300	
Maximum peak, one-cycle forward,		t = 8.3 ms	reapplied		1360	А
non-repetitive surge current	I _{FSM}	t = 10 ms	100 % V _{RRM}		1090	
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1140	
	l ² t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	8.44	kA ² s
Maximum 12t for funing		t = 8.3 ms	reapplied		7.68	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		5.97	
		t = 8.3 ms	reapplied		5.43	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms t	o 10 ms, no vol	tage reapplied	84.5	kA²√s
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % x π	$x I_{F(AV)} < I < \pi x$	$I_{F(AV)}$, $T_J = T_J$ maximum	0.74	V
High level value of threshold voltage	V _{F(TO)2}	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$			0.86	V
Low level value of forward slope resistance	r _{f1}	(16.7 % x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ maximum			3.94	mΩ
High level value of forward slope resistance	r _{f2}	$(I > \pi \times I_{F(AV)}), T_J = T_J \text{ maximum}$			3.43	11152
Maximum forward voltage drop	V_{FM}	$I_{FM} = \pi \times I_{F(A)}$	$T_J = 25 ^{\circ}C$	t _p = 400 μs square wave	1.6	V

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse leakage current	I _{RRM}	T _J = 150 °C	10	mA				
Maximum RMS insulation voltage	V _{INS}	50 Hz	3000 (1 min) 3600 (1 s)	V				



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THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Junction and storage temperature range		T _J , T _{Stg}		-40 to +150	°C			
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.33	°C/W			
Typical thermal resistance, case to heat sink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	C/ VV			
Mounting torque ± 10 % to heatsink busbar			A mounting compound is recommended and the torque should be rechecked after a period of	4	Nm			
			3 hours to allow for the spread of the compound.	3	INIII			
Approximate weight				75	g			
Approximate weight				2.7	oz.			
Case style			JEDEC®	ADD-A-PAK Ge	en 7 (TO-240AA)			

ΔR CONDUCTION PER JUNCTION											
DEVICES		SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				LINUTO
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.56	0.115	0.136	0.173	0.236	0.346	0.09	0.145	0.185	0.243	0.349	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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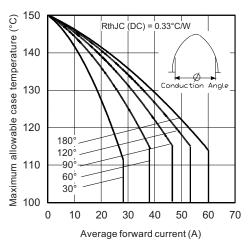


Fig. 1 - Current Ratings Characteristics

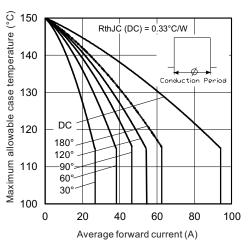


Fig. 2 - Current Ratings Characteristics

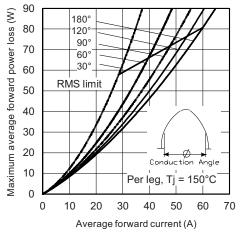


Fig. 3 - Forward Power Loss Characteristics

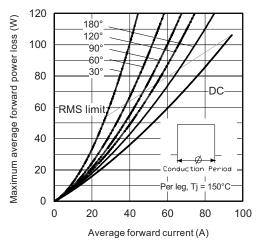
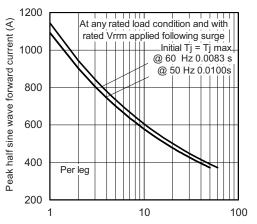


Fig. 4 - Foward Power Loss Characteristics



Number of equal amplitude half cycle current pulses (N)

Fig. 5 - Maximum Non-Repetitive Surge Current

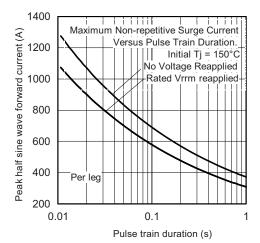


Fig. 6 - Maximum Non-Repetitive Surge Current

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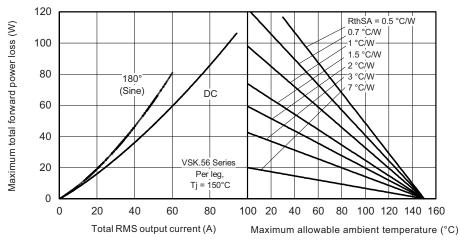


Fig. 7 - Forward Power Loss Characteristics

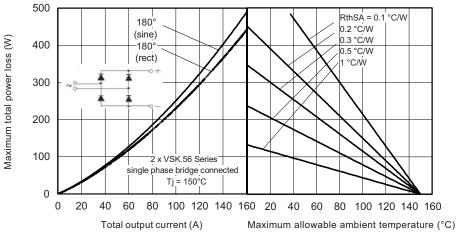


Fig. 8 - Forward Power Loss Characteristics

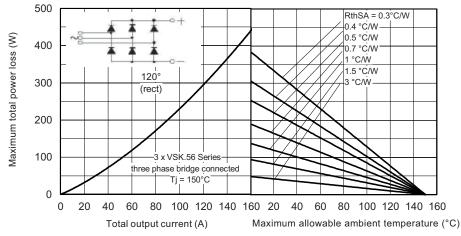


Fig. 9 - Forward Power Loss Characteristics

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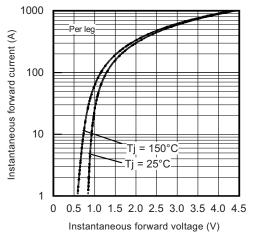


Fig. 10 - Forward Voltage Characteristics

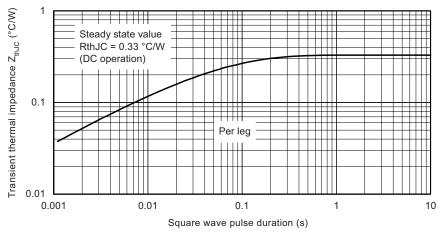
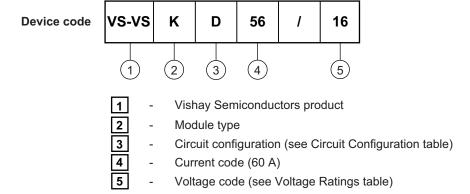


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE



Note

• To order the optional hardware go to www.vishay.com/doc?95172



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CIRCUIT CONFIGURATION						
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
		VSKD (1) ~ (2) ~ (3)				
Two diodes doubler circuit	D					
Tue diades assume attends	С	VSKC (1) 0				
Two diodes common cathode	C					
		VSKJ + +				
Two diodes common anode	J					
		VSKE				
Single diode	E					

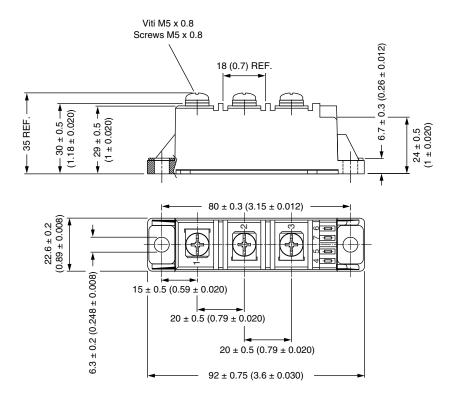
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95369			



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ADD-A-PAK Generation VII - Diode

DIMENSIONS in millimeters (inches)





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